

Characterization of active edge planar pixels produced at VTT before and after irradiation

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We will report about the characterization of FE-I3 and FE-I4 active edge planar n-in-p pixels produced at VTT, Finland. The sensor thickness is 100 μm and different geometries of the sensor edges have been implemented, down to an inactive width of only 50 μm . The charge collection properties before and after irradiation have been studied with radioactive sources and analysis of beam tests at CERN-SPS and DESY

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